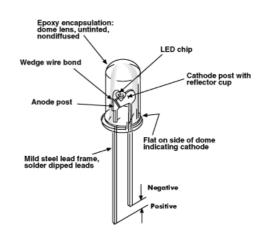
■ Features

- 385 nm UV-LED
- 5 mm clear epoxy package
- UV transparent resin
- Chip material based on GaN



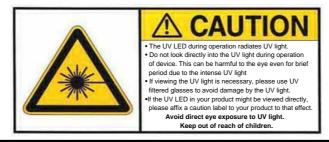
■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Value	Unit	
Power Dissipation	P _d	100	mW	
Continuous Forward Current	I _F	25	mA	
Reverse Voltage	V _R	5	V	
Operating Temperature	T _{opr}	-20 to +80	°C	
Storage Temperature	T _{stg}	-30 to +100	•C	
Soldering Temperature	T _{sol} *2	280 (with in 3 seconds)	°C	

^{*1} $~I_{FM}$ conditions : Pulse width Tw $\!\leq\! 0.1 msec.$ Duty ratio $\!\leq\! 1/10$

■ Electro-Optical Characteristics (Ta = 25°C)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Forward Voltage	V _F	I _F = 20 mA	-	3.7	4.9	V
Reverse Current	I _F	V _F = 5 V			10	μA
Radiant Flux	Po	I _F = 20 mA		2		mW
Viewing Angle	2θ _{1/2}	I _F = 20 mA		30		deg
Peak Wavelength	λ_{p}	I _F = 20 mA	380	385	388	nm
Spectrum Radiation Bandwidth	Δλ	$I_F = 20 \text{ mA}$		18		nm



^{*2} Soldering portion of lead: 3mm from bottom face of resin package.